

DC-18.0 GHz GaAs MMIC 5-Bit Digital Attenuator



August 2007 - Rev 21-Aug-07

X A1000-BD

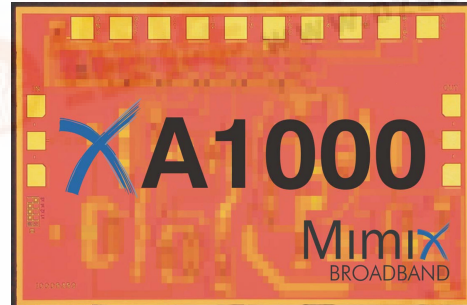
Features

- X 5-Bit Attenuator
- X 27.9 dB Attenuation Range
- X 24 dBm P1dB Input Compression
- X 0.9 dB LSB
- X Digital Control (0.0 to 3.3 V)
- X 100% On-Wafer RF, DC and Noise Figure Testing
- X 100% Visual Inspection to MIL-STD-883 Method 2010

General Description

Mimix Broadband's DC- 18.0 GHz attenuator has an LSB value of 0.9 dB and is controlled with 5 digital binary inputs, which meet the LVCMOS specifications. The 2.4 x 1.6 mm² device uses a single supply voltage of -7.5 V. This MMIC uses Mimix Broadband's 0.5 μm GaAs PHEMT device model technology, and is based upon optical gate lithography to ensure high repeatability and uniformity. The chip has surface passivation to protect and provide a rugged part with backside via holes and gold metallization to allow either a conductive epoxy or eutectic solder die attach process. This device is well suited for radar and applications.

Chip Device Layout



Absolute Maximum Ratings

| | |
|---|--------------------------------|
| Supply Voltage (V _{ss}) | -10.0 VDC |
| Supply Current (I _{ss}) | 10.0 mA |
| Input Power (P _{in}) | 30.0 dBm |
| Storage Temperature (T _{stg}) | -65 to +165 °C |
| Operating Temperature (T _a) | -55 to MTTF Table ³ |
| Channel Temperature (T _{ch}) | MTTF Table ³ |

(3) Channel temperature affects a device's MTBF. It is recommended to keep channel temperature as low as possible for maximum life.

Electrical Characteristics (Ambient Temperature T = 25 °C)

| Parameter | Units | Min. | Typ. | Max. |
|---|-------|------|------|------|
| Frequency Range (f) | GHz | DC | - | 18.0 |
| Attenuation Range | dB | - | 27.9 | - |
| Insertion Loss @ 10 GHz (S ₂₁), Reference Level | dB | - | 5.5 | - |
| Input Return Loss (S ₁₁), All States | dB | - | 17.0 | - |
| Output Return Loss (S ₂₂), All States | dB | - | 15.0 | - |
| Input Power at 1 dB Compression (P _{1dB}) | dBm | 24.0 | 25.0 | - |
| RMS Attenuation Error | dB | - | <0.5 | - |
| Max Attenuation Error | dB | - | <1 | - |
| RMS Phase Error | deg | - | <10 | - |
| Max Phase Error | deg | - | <20 | - |
| Phase Variation @ 10 GHz | deg | - | 15 | - |
| Switching Speed | nS | - | - | 45.0 |
| V _{ss} | VDC | - | -7.5 | - |
| I _{ss} | mA | - | 9 | - |
| V _{control High} | V | 3.3 | | 5 |
| V _{control Low} | V | 0 | | 0.8 |



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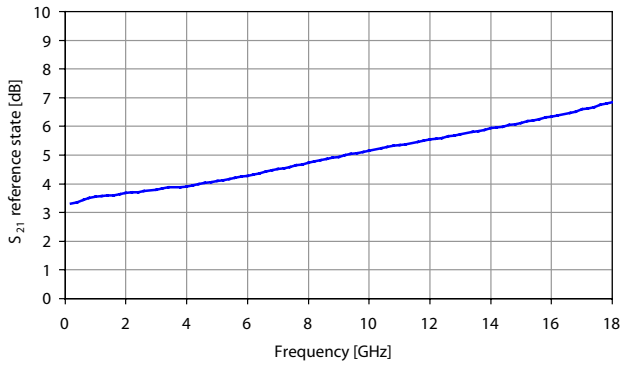


August 2007 - Rev 21-Aug-07

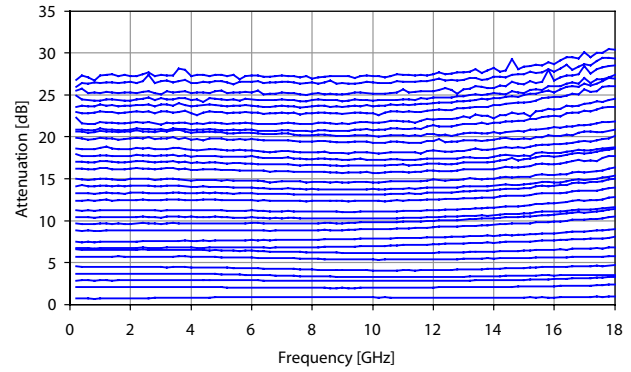
A1000-BD

Attenuator Measurements

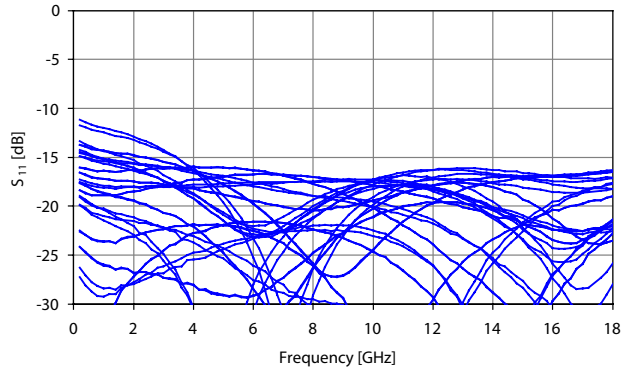
Insertion Loss - Reference State



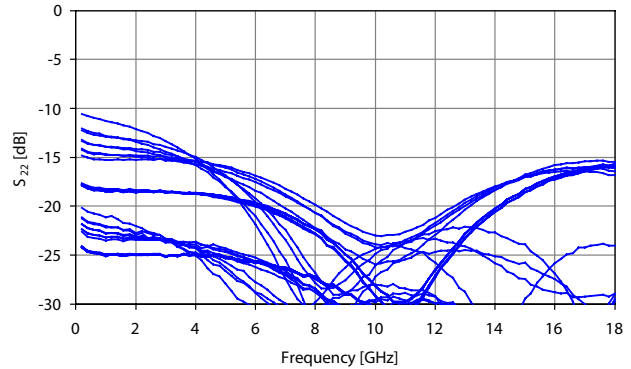
Attenuation - All States



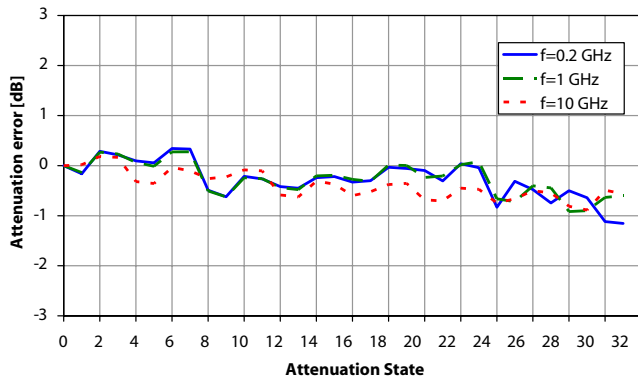
Input Return Loss - All States



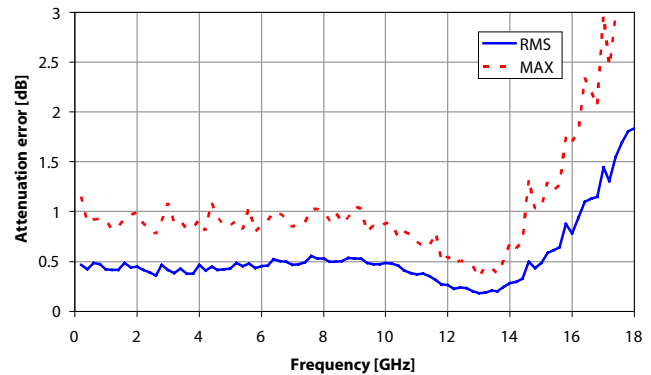
Output Return Loss - All States



Attenuation Error vs State



Attenuation Error



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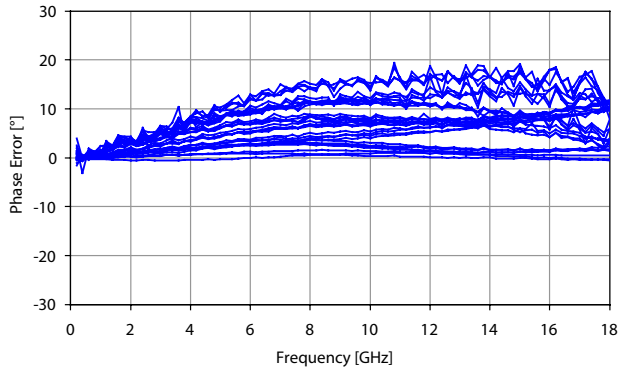


August 2007 - Rev 21-Aug-07

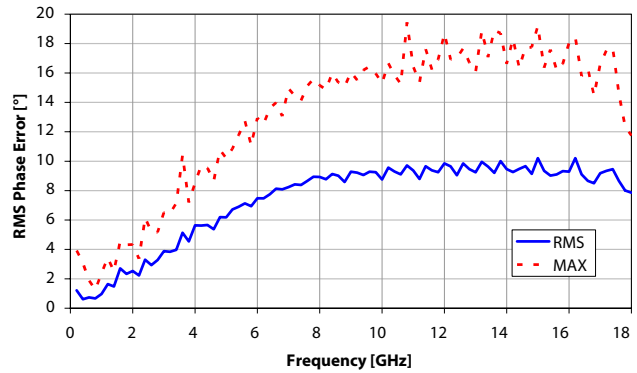
A1000-BD

Attenuator Measurements (cont.)

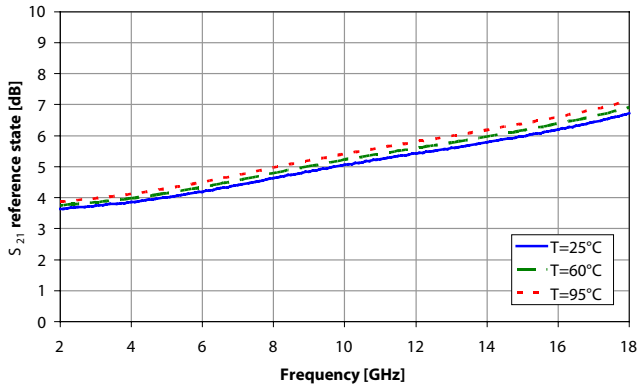
Phase Error - All States



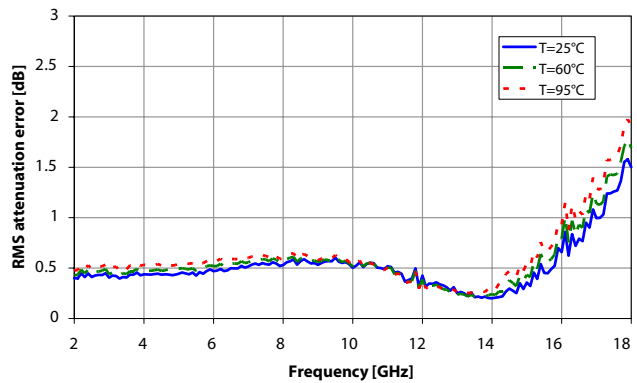
Phase Error



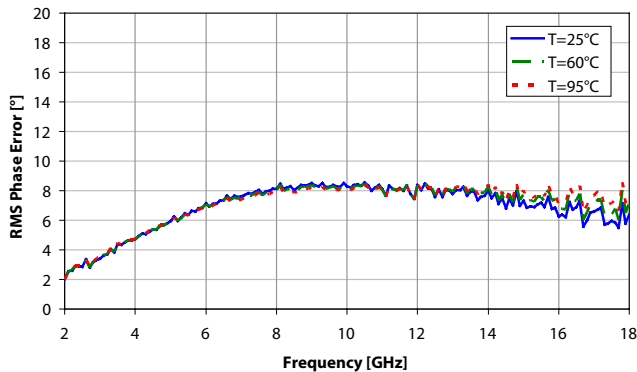
Insertion Loss vs Temp - Reference State



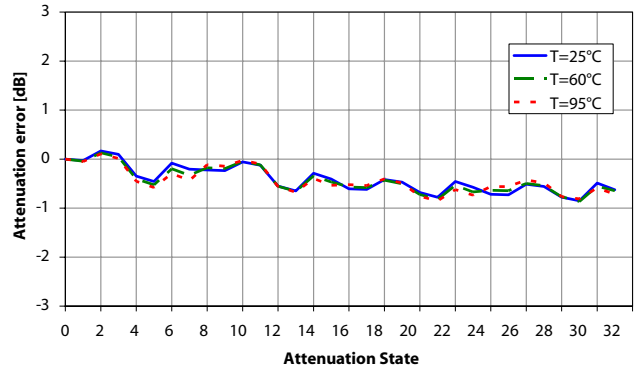
RMS Attenuation Error vs Temp



RMS Phase Error vs Temp



Attenuation Error at 10 GHz vs Temp



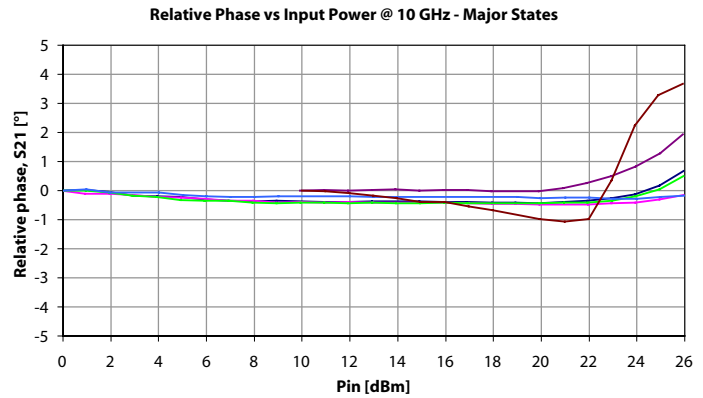
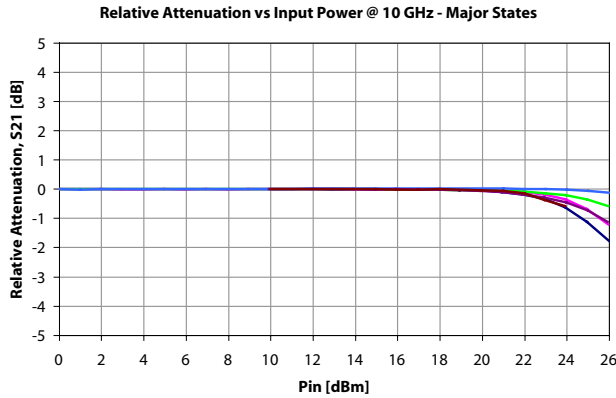
DC-18.0 GHz GaAs MMIC 5-Bit Digital Attenuator



August 2007 - Rev 21-Aug-07

A1000-BD

Attenuator Measurements (cont.)



Logic Truth Table - Major States

| Attenuation Level (dB) | I1 | I2 | I3 | I4 | I5 |
|------------------------|----|----|----|----|----|
| 0 | 0 | 0 | 0 | 0 | 0 |
| 0.9 | 1 | 0 | 0 | 0 | 0 |
| 1.8 | 0 | 1 | 0 | 0 | 0 |
| 3.6 | 0 | 0 | 1 | 0 | 0 |
| 7.2 | 0 | 0 | 0 | 1 | 0 |
| 14.4 | 0 | 0 | 0 | 0 | 1 |
| - | - | - | - | - | - |
| 27.9 | 1 | 1 | 1 | 1 | 1 |

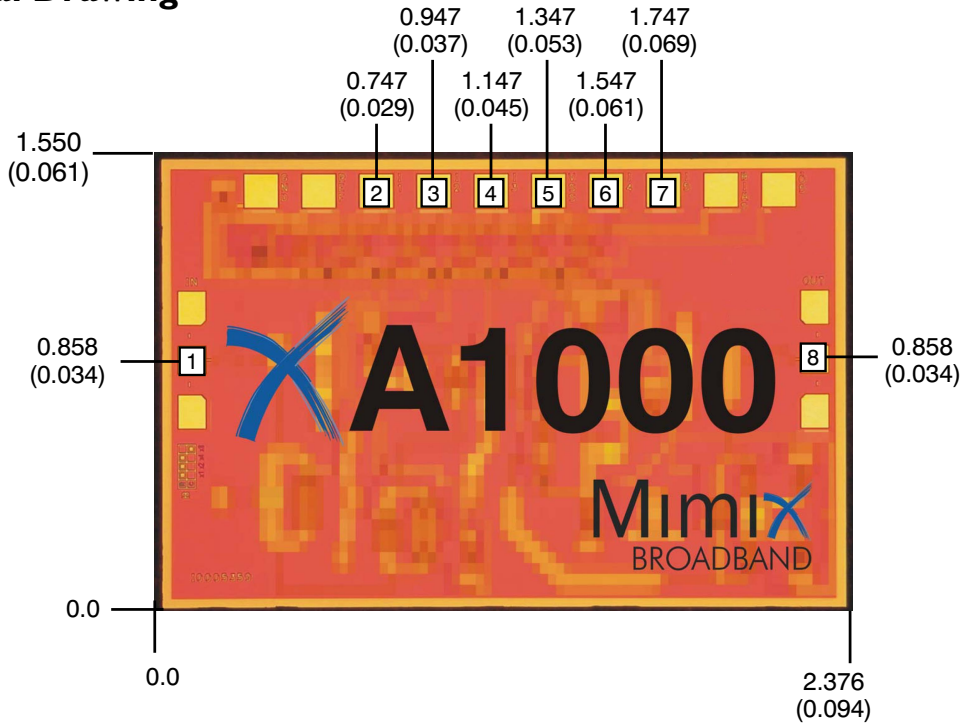
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August 2007 - Rev 21-Aug-07

X A1000-BD

Mechanical Drawing



(Note: Engineering designator is I0005359)

Units: millimeters (inches) Bond pad dimensions are shown to center of bond pad.
 Thickness: 0.110 +/- 0.010 (0.0043 +/- 0.0004), Backside is ground, Bond Pad/Backside Metallization: Gold
 All Bond Pads are 0.100 x 0.100 (0.004 x 0.004).
 Bond pad centers are approximately 0.109 (0.004) from the edge of the chip.
 Dicing tolerance: +/- 0.005 (+/- 0.0002). Approximate weight: 2.28 mg.

| | | | |
|-----------------------|-----------------------|-----------------------|-----------------------|
| Bond Pad #1 (RF In) | Bond Pad #3 (Input 2) | Bond Pad #5 (Vss) | Bond Pad #7 (Input 5) |
| Bond Pad #2 (Input 1) | Bond Pad #4 (Input 3) | Bond Pad #6 (Input 4) | Bond Pad #8 (RF Out) |

Bias Arrangement

Bypass Capacitors - See App Note [2]

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August 2007 - Rev 21-Aug-07

 **AI000-BD**

Handling and Assembly Information

CAUTION! - Mimix Broadband MMIC Products contain gallium arsenide (GaAs) which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- *Do not ingest.*
- *Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.*
- *Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.*

Life Support Policy - Mimix Broadband's products are not authorized for use as critical components in life support devices or systems without the express written approval of the President and General Counsel of Mimix Broadband. As used herein: (1) Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user. (2) A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ESD - Gallium Arsenide (GaAs) devices are susceptible to electrostatic and mechanical damage. Die are supplied in anti-static containers, which should be opened in cleanroom conditions at an appropriately grounded antistatic workstation. Devices need careful handling using correctly designed collets, vacuum pickups or, with care, sharp tweezers.

Die Attachment - GaAs Products from Mimix Broadband are 0.100 mm (0.004") thick and have vias through to the back-side to enable grounding to the circuit. Microstrip substrates should be brought as close to the die as possible. The mounting surface should be clean and flat. If using conductive epoxy, recommended epoxies are Tanaka TS3332LD, Die Mat DM6030HK or DM6030HK-Pt cured in a nitrogen atmosphere per manufacturer's cure schedule. Apply epoxy sparingly to avoid getting any on to the top surface of the die. An epoxy fillet should be visible around the total die periphery. For additional information please see the Mimix "Epoxy Specifications for Bare Die" application note. If eutectic mounting is preferred, then a fluxless gold-tin (AuSn) preform, approximately 0.001² thick, placed between the die and the attachment surface should be used. A die bonder that utilizes a heated collet and provides scrubbing action to ensure total wetting to prevent void formation in a nitrogen atmosphere is recommended. The gold-tin eutectic (80% Au 20% Sn) has a melting point of approximately 280° C (Note: Gold Germanium should be avoided). The work station temperature should be 310°C +/- 10° C. Exposure to these extreme temperatures should be kept to minimum. The collet should be heated, and the die pre-heated to avoid excessive thermal shock. Avoidance of air bridges and force impact are critical during placement.

Wire Bonding - Windows in the surface passivation above the bond pads are provided to allow wire bonding to the die's gold bond pads. The recommended wire bonding procedure uses 0.076 mm x 0.013 mm (0.003" x 0.0005") 99.99% pure gold ribbon with 0.5-2% elongation to minimize RF port bond inductance. Gold 0.025 mm (0.001") diameter wedge or ball bonds are acceptable for DC Bias connections. Aluminum wire should be avoided. Thermo-compression bonding is recommended though thermosonic bonding may be used providing the ultrasonic content of the bond is minimized. Bond force, time and ultrasonics are all critical parameters. Bonds should be made from the bond pads on the die to the package or substrate. All bonds should be as short as possible.

Ordering Information

XA1000-BD-000V Where "V" is RoHS compliant die packed in vacuum release gel paks
XA1000-BD-EV1 XA1000 die evaluation module